PF01411B

MOS FET Power Amplifier Module for E-GSM Handy Phone

HITACHI

ADE-208-434B (Z) 3rd Edition November 1, 1997

Application

- For E-GSM class4 880 to 915 MHz
- For 3.5 V nominal battery use

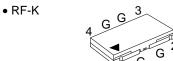
Features

• High gain 3stage amplifier: 0 dBm input

• Lead less thin & Small package: 2 mm Max, 0.2cc

High efficiency: 45% Typ at 35.5 dBmWide gain control range: 70 dB Typ

Pin Arrangement



1: Pin 2: Vapc 3: Vdd 4: Pout G: GND

Absolute Maximum Ratings $(Tc = 25^{\circ}C)$

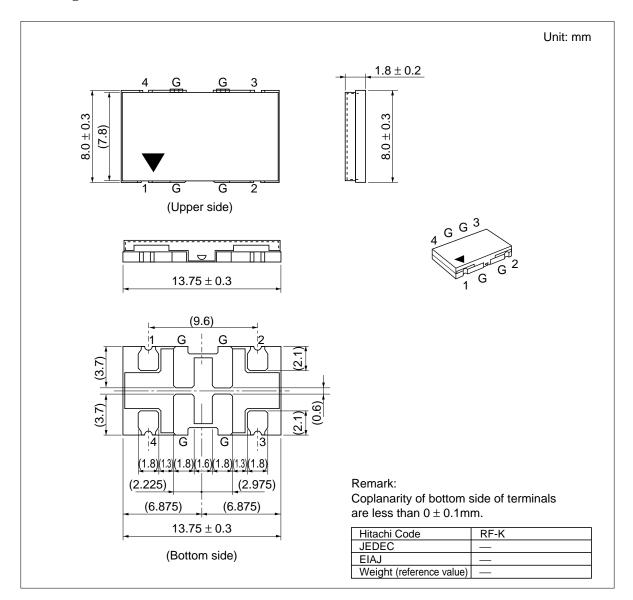
Item	Symbol	Rating	Unit	
Supply voltage	V_{DD}	8	V	
Supply current	I _{DD}	3	Α	
V _{APC} voltage	V _{APC}	4	V	
Input power	Pin	10	mW	
Operating case temperature	Tc (op)	−30 to +100	°C	
Storage temperature	Tstg	-30 to +100	°C	
Output power	Pout	5	W	

PF01411B

Electrical Characteristics (Tc = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	880	_	915	MHz	
Control voltage range	V_{APC}	0.5	_	2.2	V	
Drain cutoff current	I _{DS}	_	_	100	μΑ	$V_{DD} = 8 \text{ V}, V_{APC} = 0 \text{ V}$
Total efficiency	$\eta_{\scriptscriptstyle T}$	40	45	_	%	$Pin = 0 dBm, V_{DD} = 3.5 V,$
2nd harmonic distortion	2nd H.D.	_	-45	-35	dBc	Pout = 35.5 dBm,
3rd harmonic distortion	3rd H.D.	_	-45	-35	dBc	Vapc = controlled,
Input VSWR	VSWR (in)		1.5	3	_	$R_L = Rg = 50 \Omega$, $Tc = 25^{\circ}C$
Output power (1)	Pout (1)	35.5	36.0	_	dBm	$\begin{aligned} &\text{Pin} = 0 \text{ dBm}, \text{ V}_{\text{DD}} = 3.5 \text{ V}, \\ &\text{V}_{\text{APC}} = 2.2 \text{ V}, \text{ R}_{\text{L}} = \text{Rg} = 50 \Omega, \\ &\text{Tc} = 25^{\circ}\text{C} \end{aligned}$
Output power (2)	Pout (2)	33.5	34.2	_	dBm	$\begin{aligned} &\text{Pin} = 0 \text{ dBm, V}_{\text{DD}} = 3.0 \text{ V,} \\ &\text{V}_{\text{APC}} = 2.2 \text{ V, R}_{\text{L}} = \text{Rg} = 50 \Omega, \\ &\text{Tc} = 85^{\circ}\text{C} \end{aligned}$
Isolation	_		-40	-36	dBm	$Pin = 0 dBm, V_{DD} = 3.5 V,$ $V_{APC} = 0.5 V, R_{L} = Rg = 50 Ω,$ Tc = 25°C
Switching time	tr, tf		1	2	μs	Pin = 0 dBm, V_{DD} = 3.5 V, Pout = 0 to 35.5 dBm, R_L = Rg = 50 Ω, Tc = 25°C
Stability	_	No pa	No parasitic oscillation		_	Pin = 0 dBm, V_{DD} = 3 to 5.1 V, Pout \leq 35.5 dBm, Vapc \leq 2.2 V GSM pulse. Rg = 50 Ω , Tc = 25°C, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	_	No degradation		_	Pin = 0 dBm, V_{DD} = 3 to 5.1 V, Pout \leq 35.5 dBm, Vapc \leq 2.2 V GSM pulse. Rg = 50 Ω , t = 20 sec., Tc = 25°C, Output VSWR = 10 : 1 All phases	

Package Dimensions



When using this document, keep the following in mind:

- 1. This document may, wholly or partially, be subject to change without notice.
- 2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
- 3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
- 4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described
- 5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
- 6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.

Semiconductor & IC Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd. Semiconductor & IC Div. 2000 Sierra Point Parkway Brisbane, CA. 94005-1835

Tel: 415-589-8300

Fax: 415-583-4207

Hitachi Europe GmbH Electronic Components Group Continental Europe Dornacher Stra§e 3 D-85622 Feldkirchen M nchen

Tel: 089-9 91 80-0

Fax: 089-9 29 30 00

Hitachi Europe Ltd. Electronic Components Div. Northern Europe Headquarters Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA United Kingdom

Tel: 0628-585000 Fax: 0628-778322 Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 0104 Tel: 535-2100

Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd. Unit 706. North Tower. World Finance Centre, Harbour City, Canton Road Tsim Sha Tsui, Kowloon Hong Kong

Tel: 27359218 Fax: 27306071

Copyright ' Hitachi, Ltd., 1997. All rights reserved. Printed in Japan.